MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PLED

MMBT2222

Product specification





FEATURES

- Epitaxial planar die construction
- Complementary PNP Type available(MMBT2907)

Reference News

| PACKAGE OUTLINE | | MARKING | |
|-----------------|--------------------------------|---------|--|
| 1 2 3 | 1. BASE 2. EMITTER 3.COLLECTOR | 1P | |
| SOT-23 | | | |

MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

| Symbol | Parameter | Value | Unit |
|----------------------|--|----------|------|
| V _{CBO} | Collector-Base Voltage | 75 | V |
| V _{CEO} | Collector-Emitter Voltage | 40 | V |
| V _{EBO} | Emitter-Base Voltage | 6 | V |
| lc | Collector Current -Continuous | 600 | mA |
| Pc | Collector Dissipation | 300 | mW |
| R _{eJA} | Thermal Resistance, Junction to Ambient | 417 | °C/W |
| T _J ,Tstg | Operation Junction and Storage Temperature Range | -55~+150 | °C |

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

| Pa rameter | Symbol | Test conditions | Min | Тур | Max | Unit |
|--------------------------------------|------------------------|---|-----|-----|------------|------|
| Collector-base breakdown voltage | V _{(BR)CBO} | l _C = 10μA, I _E =0 | 75 | | | V |
| Collector-emitter breakdown voltage | V _{(BR)CEO} * | Ic= 10mA, I _B =0 | 40 | | | V |
| Emitter-base breakdown voltage | V _{(BR)EBO} | l∈=10μA, I _C =0 | 6 | | | V |
| Collector cut-off current | I _{CBO} | V _{CB} =60V, I _E =0 | | | 0.01 | μA |
| Collector cut-off current | Icex | V _{CE} =30V,V _{BE(off)} =3V | | | 0.01 | μA |
| Emitter cut-off current | I _{EBO} | V _{EB} = 3V, I _C =0 | | | 0.1 | μA |
| DC current gain | h _{FE(1)} * | V _{CE} =10V, I _C = 150mA | 100 | | 300 | |
| | h _{FE(2)} | V _{CE} =10V, I _C = 0.1mA | 40 | | | |
| | h _{FE(3)} * | V _{CE} =10V, I _C = 500mA | 42 | | | |
| Collector-emitter saturation voltage | V _{CE(sat)} * | l _C =500 mA, I _B = 50mA l _C =150 mA, I _B =15mA | | | 1 0.3 | V |
| Base-emitter saturation voltage | V _{BE(sat)} * | I_C =500 mA, I_B = 50mA I_C = 150 mA, I_B =15mA | | | 2.0 1.2 | V |
| Transition frequency | f⊤ | V _{CE} =20V, I _C = 20mA, f=100MHz | 300 | | | MHz |
| Delay time | t _d | V _{CC} =30V, V _{BE(off)} =-0.5V | | | 10 | ns |
| Rise time | tr | Ic=150mA , I _{B1} = 15mA | | | 25 | ns |
| Storage time | ts | Vcc=30V, Ic=150mA | | | 225 | ns |
| Fall time | t _f | I _{B1} =-I _{B2} =15mA | | | 60 | ns |

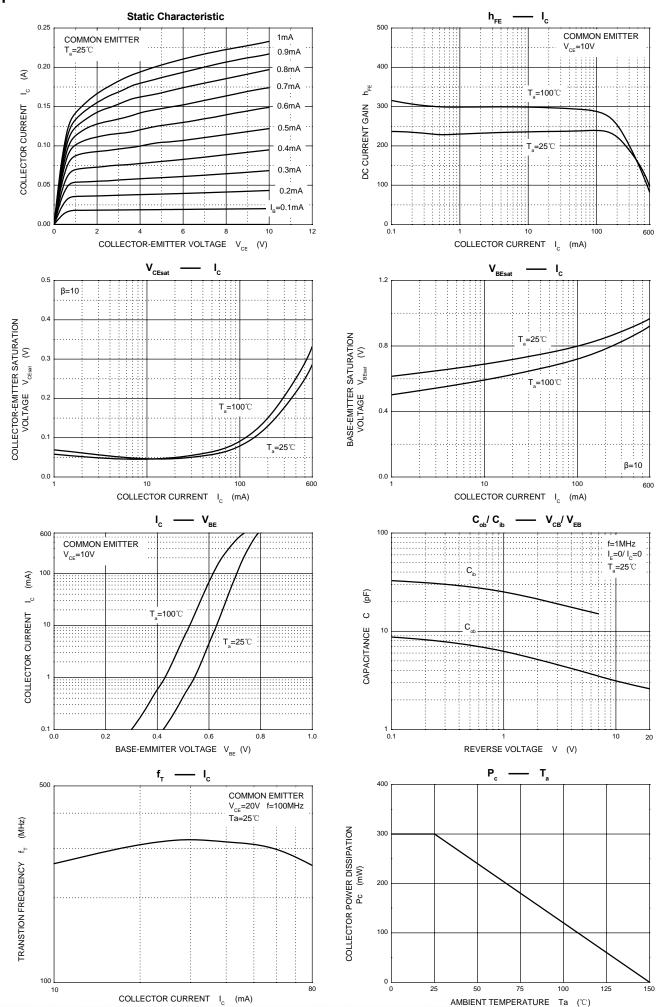
*pulse test: Pulse Width ≤300µs, Duty Cycle≤ 2.0%.

CLASSIFICATION OF h_{FE(1)}

| RANK | L | Н |
|-------|----------|----------|
| RANGE | 100 –200 | 200 –300 |

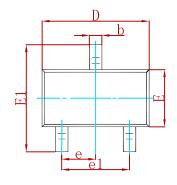


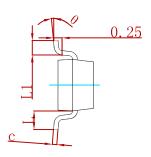
Typical Characteristics

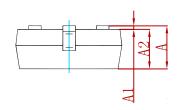




PACKAGE MECHANICAL DATA

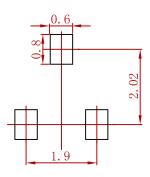






| Cumbal | Dimensions In Millimeters | | Dimensions In Inches | | |
|--------|---------------------------|-------|----------------------|-------|--|
| Symbol | Min | Max | Min | Max | |
| Α | 0.900 | 1.150 | 0.035 | 0.045 | |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 | |
| A2 | 0.900 | 1.050 | 0.035 | 0.041 | |
| b | 0.300 | 0.500 | 0.012 | 0.020 | |
| С | 0.080 | 0.150 | 0.003 | 0.006 | |
| D | 2.800 | 3.000 | 0.110 | 0.118 | |
| Е | 1.200 | 1.400 | 0.047 | 0.055 | |
| E1 | 2.250 | 2.550 | 0.089 | 0.100 | |
| е | 0.950 TYP | | 0.037 | 7 TYP | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 | |
| L | 0.550 REF | | 0.022 | 2 REF | |
| L1 | 0.300 | 0.500 | 0.012 | 0.020 | |
| θ | 0° | 8° | 0° | 8° | |

Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

| P/N | PKG | QTY |
|----------|--------|------|
| MMBT2222 | SOT-23 | 3000 |



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